


**HIGH DENSITY MOUNTING
PHOTODARLINGTON
OPTICALLY COUPLED ISOLATORS**
**APPROVALS**

- UL recognised, File No. E91231

DESCRIPTION

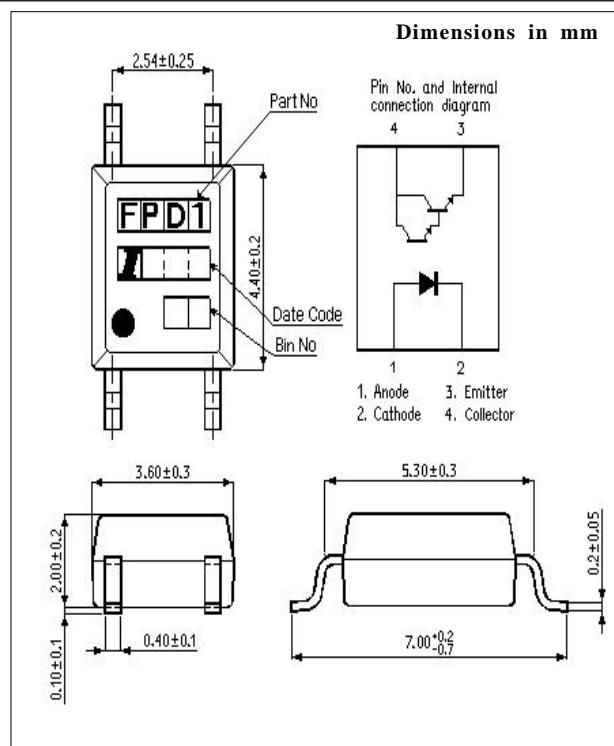
The IS2702-1 is an optically coupled isolator consisting of an infrared light emitting diode and NPN silicon photodarlington in a space efficient dual in line plastic package.

FEATURES

- Marked as FPD1.
- Current Transfer Ratio MIN. 600%
- Isolation Voltage ($3.75\text{kV}_{\text{RMS}}, 5.3\text{kV}_{\text{PK}}$)
- All electrical parameters 100% tested
- Drop in replacement for NEC PS2702-1

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



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ABSOLUTEMAXIMUMRATINGS
(25°C unless otherwise specified)

Storage Temperature	—	-55°C to + 150°C
Operating Temperature	—	-55°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)		260°C

INPUTDIODE

Forward Current	—	50mA
Reverse Voltage	—	6V
Power Dissipation	—	70mW

OUTPUTTRANSISTOR

Collector-emitter Voltage BV _{CEO}	—	35V
Emitter-collector Voltage BV _{ECO}	—	6V
Collector Current	—	80mA
Power Dissipation	—	150mW

POWERDISSIPATION

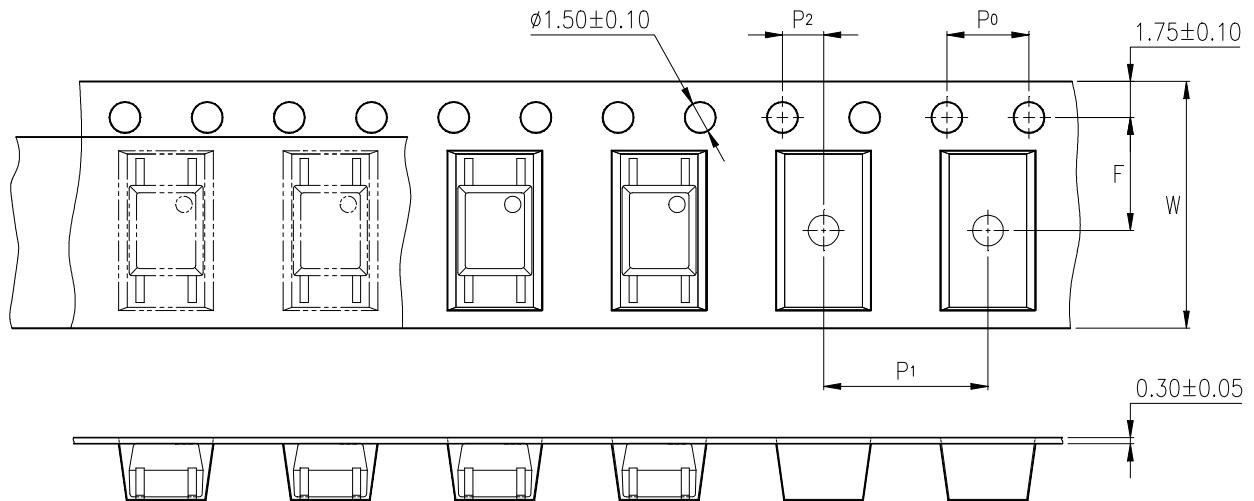
Total Power Dissipation	—	170mW
(derate linearly 2.26mW/°C above 25°C)		

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V _F)		1.2	1.4	V	I _F =20mA
	Reverse Current (I _R)			10	μA	V _R =4V
Output	Collector-emitter Breakdown (BV _{CEO})	35			V	I _C =0.1mA
	Emitter-collector Breakdown (BV _{ECO})	6			V	I _E = 10uA
Coupled	Collector-emitter Dark Current (I _{CEO})			1	uA	V _{CE} =10V
	Current Transfer Ratio (CTR)	600		7500	%	1mA I _F , 2V V _{CE}
	Collector-emitter Saturation Voltage V _{CE(SAT)}			1	V	20mA I _F , 5mA I _C
	Input to Output Isolation Voltage V _{ISO}	3750 5300			V _{RMS} V _{PK}	See note 1 See note 1
	Input-output Isolation Resistance R _{ISO}	5x10 ¹⁰			Ω	V _{IO} = 500V (note 1)
	Output Rise Time tr Output Fall Time tf		60 53	300 250	μs	V _{CE} =2V, I _C =10mA, R _L =100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.

TAPING DIMENSIONS



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	$12 \pm 0.3 (.47)$
Pitch of sprocket holes	P_0	$4 \pm 0.1 (.15)$
Distance of compartment	F	$5.5 \pm 0.1 (.217)$
Distance of compartment to compartment	P_2	$2 \pm 0.1 (.079)$
Distance of compartment to compartment	P_1	$8 \pm 0.1 (.315)$

CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

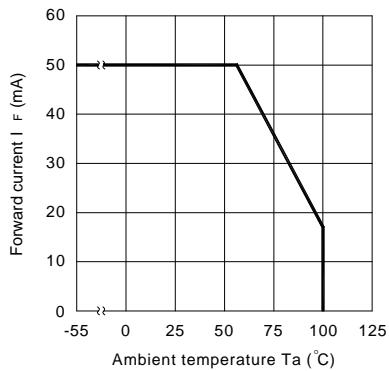


Fig.2 Collector Power Dissipation vs. Ambient Temperature

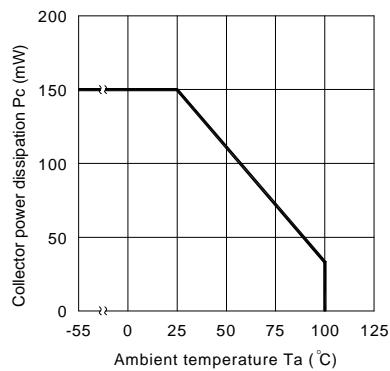


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

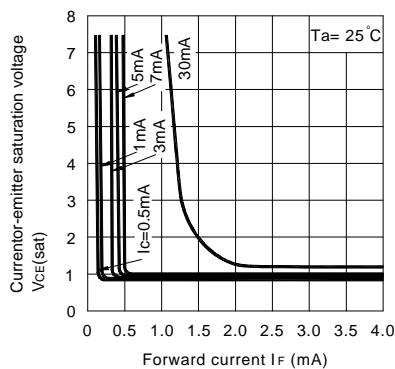


Fig.4 Forward Current vs. Forward Voltage

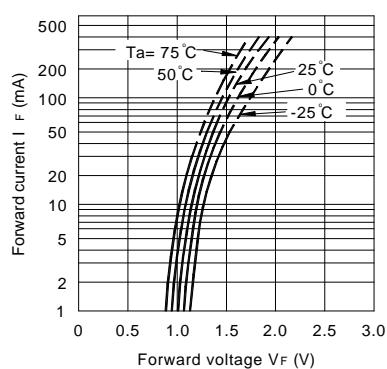


Fig.5 Current Transfer Ratio vs. Forward Current

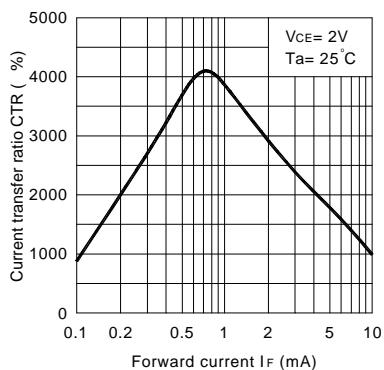
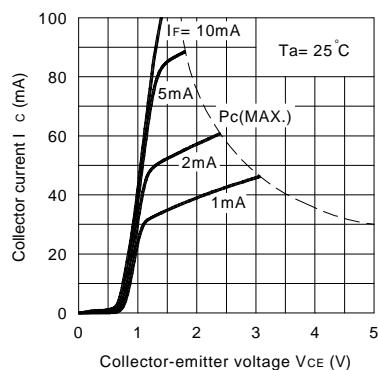


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

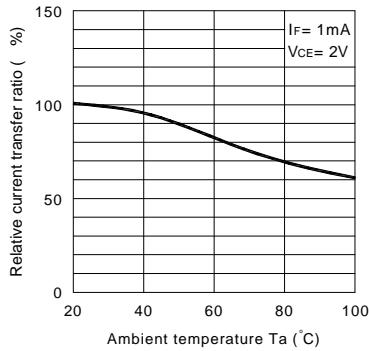


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

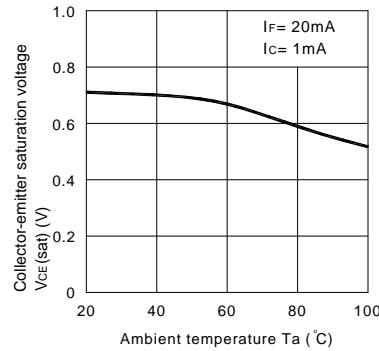


Fig.9 Collector Dark Current vs. Ambient Temperature

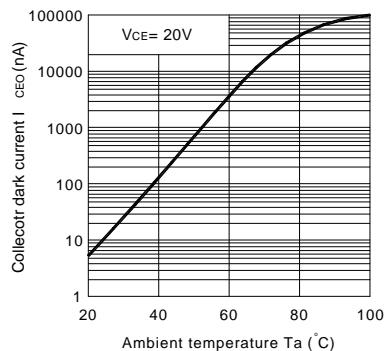


Fig.10 Response Time vs. Load Resistance

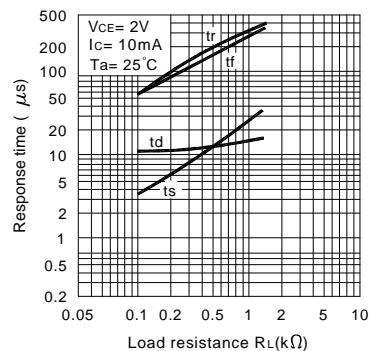
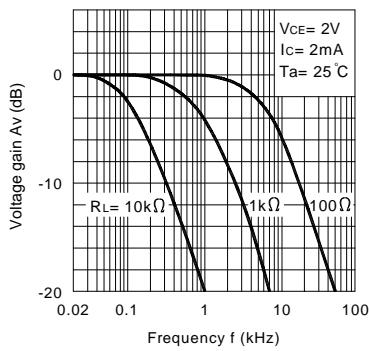
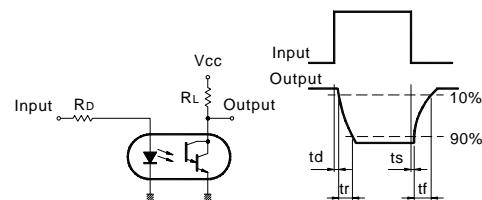


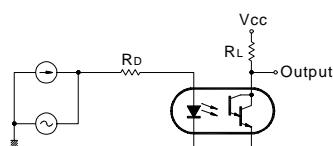
Fig.11 Frequency Response



Test Circuit for Response Time

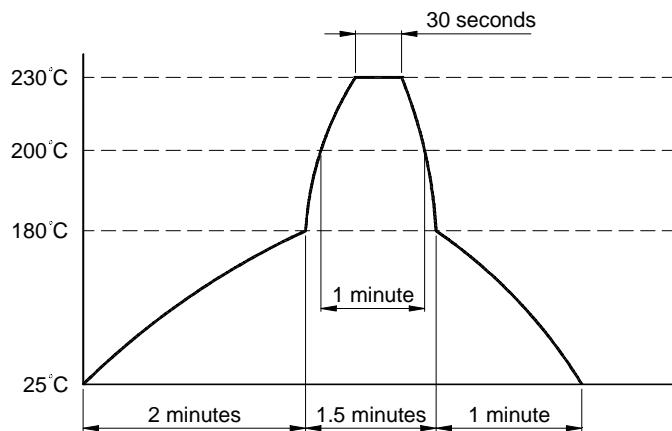


Test Circuit for Frequency Response



TEMPERATURE PROFILE OF SOLDERING REFLOW

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.
Keep the temperature on the package of the device within the condition of above (1).